

EAST - [10.717146.wsp:1]

FileViewEditToolsWindowHelp

Drafts

BRS:

BRS:

Pending

Active

L2: (1562489) FeRAM or FEDRAM or FRAM or (ferroelectric ajd3 memory)

L3: (6821) precharg\$4 near3 (bitline or (bit adj line) or (bit-line))

L4: (216) plateline or plate-line

L5: (19) 3 same 4

L6: (67) 3 and 4

L7: (48) 6 not 5

L30: (6603) 2 and 3

L32: (1548) 30 and 365/203

L33: (373) 30 and 365/145

L34: (836) 30 and 365/149

L41: (262) 32 and plate

L42: (296) 33 and plate

L43: (452) 34 and plate

L44: (234) 42 not 41

L45: (210) 43 not (41 or 42)

Failed

Saved

Search

USPAT: US-PGPUB: EPO: JPO: DERWENT: IBM_TDB

Default operator: OR

Highlight all hit terms initially

	U	1	Document ID	Issue Date	Inventor	Current OR	Current XRe	Retrieval C	Title	Page	S	C	P	3
1	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 5675530 A	19971007	Hirano, Hiroshige et al.	365/145	365/149; 365/190		Ferroelectric memory device	27	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>
2	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 5467302 A	19951114	Hirano, Hiroshige et al.	365/145	365/189.01		Semiconductor memory device	35	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>

Ready

Start

eDAN.V...

Client M...

Calendar...

Docume...

Explorin...

Random ...

EAST: [..]

Docume...

EAST: Br...

EN - EUR...

8:40 PM